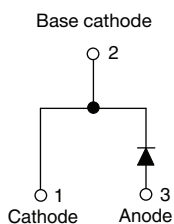


# 650 V Power SiC Merged PIN Schottky Diode, 20 A



## FEATURES

- Majority carrier diode using Schottky technology on SiC wide band gap material
- Positive  $V_F$  temperature coefficient for easy paralleling
- Virtually no recovery tail and no switching losses
- Temperature invariant switching behavior
- 175 °C maximum operating junction temperature
- MPS structure for high ruggedness to forward current surge events
- Meets JESD 201 class 1A whisker test
- Solder Bath temperature 275 °C maximum, 10 s per JESD 22-B106
- Material categorization: for definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)



**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**

## LINKS TO ADDITIONAL RESOURCES



| PRIMARY CHARACTERISTICS  |             |
|--------------------------|-------------|
| $I_{F(AV)}$              | 20 A        |
| $V_R$                    | 650 V       |
| $V_F$ at $I_F$ at 150 °C | 1.6 V       |
| $T_J$ max.               | 175 °C      |
| $I_R$ at $V_R$ at 175 °C | 35 $\mu$ A  |
| $Q_C$ ( $V_R = 400$ V)   | 68 nC       |
| Package                  | 2L TO-220AC |
| Circuit configuration    | Single      |

## DESCRIPTION / APPLICATIONS

Wide band gap SiC based 650 V Schottky diode, designed for high performance and ruggedness.

Optimum choice for high speed hard switching and efficient operation over a wide temperature range, it is also recommended for all applications suffering from Silicon ultrafast recovery behavior.

Typical applications include AC/DC PFC and DC/DC ultra high frequency output rectification in FBPS and LLC converters.

## MECHANICAL DATA

**Case:** 2L TO-220AC

Molding compound meets UL 94 V-0 flammability rating  
Base P/N-M3 - halogen-free, RoHS-compliant

**Terminals:** matte tin plated leads, solderable per J-STD-002 and JESD 22-B102

**Mounting torque:** 10 in-lbs maximum

| ABSOLUTE MAXIMUM RATINGS ( $T_A = 25$ °C unless otherwise specified) |                      |                                                    |             |                  |
|----------------------------------------------------------------------|----------------------|----------------------------------------------------|-------------|------------------|
| PARAMETER                                                            | SYMBOL               | TEST CONDITIONS                                    | VALUES      | UNITS            |
| Peak repetitive reverse voltage                                      | $V_{RRM}$            |                                                    | 650         | V                |
| Average rectified forward current                                    | $I_{F(AV)}$          | $T_C = 125$ °C (DC)                                | 20          | A                |
| DC blocking voltage                                                  | $V_{DC}$             |                                                    | 650         | V                |
| Repetitive peak surge current                                        | $I_{FRM}$            | $T_C = 25$ °C, $f = 50$ Hz, square wave, DC = 25 % | 75          | A                |
| Non-repetitive peak forward surge current                            | $I_{FSM}$            | $T_C = 25$ °C, $t_p = 10$ ms, half sine wave       | 160         |                  |
|                                                                      |                      | $T_C = 110$ °C, $t_p = 10$ ms, half sine wave      | 140         |                  |
| Power dissipation                                                    | $P_{tot}^{(1)}$      | $T_C = 25$ °C                                      | 119         | W                |
|                                                                      |                      | $T_C = 110$ °C                                     | 52          |                  |
| $I^2t$ value                                                         | $\int i^2 dt$        | $T_C = 25$ °C                                      | 128         | A <sup>2</sup> s |
|                                                                      |                      | $T_C = 110$ °C                                     | 98          |                  |
| Operating junction and storage temperatures                          | $T_J^{(2)}, T_{Stg}$ |                                                    | -55 to +175 | °C               |

## Notes

(1) Based on maximum  $R_{th}$

(2) The heat generated must be less than the thermal conductivity from junction-to-ambient:  $dP_D/dT_J < 1/R_{thJA}$

**ELECTRICAL SPECIFICATIONS** ( $T_J = 25\text{ }^{\circ}\text{C}$  unless otherwise specified)

| PARAMETER               | SYMBOL | TEST CONDITIONS                                             | MIN. | TYP. | MAX. | UNITS         |
|-------------------------|--------|-------------------------------------------------------------|------|------|------|---------------|
| Forward voltage         | $V_F$  | $I_F = 20\text{ A}$                                         | -    | 1.45 | 1.70 | V             |
|                         |        | $I_F = 20\text{ A}, T_J = 150\text{ }^{\circ}\text{C}$      | -    | 1.60 | 1.90 |               |
|                         |        | $I_F = 20\text{ A}, T_J = 175\text{ }^{\circ}\text{C}$      | -    | 1.65 | -    |               |
| Reverse leakage current | $I_R$  | $V_R = V_R\text{ rated}$                                    | -    | -    | 100  | $\mu\text{A}$ |
|                         |        | $V_R = V_R\text{ rated}, T_J = 150\text{ }^{\circ}\text{C}$ | -    | -    | 250  |               |
|                         |        | $V_R = V_R\text{ rated}, T_J = 175\text{ }^{\circ}\text{C}$ | -    | 35   | -    |               |
| Total capacitance       | C      | $V_R = 1\text{ V}, f = 1\text{ MHz}$                        | -    | 1050 | -    | pF            |
|                         |        | $V_R = 400\text{ V}, f = 1\text{ MHz}$                      | -    | 105  | -    |               |
| Total capacitive charge | $Q_C$  | $V_R = 400\text{ V}, f = 1\text{ MHz}$                      | -    | 68   | -    | nC            |

**THERMAL - MECHANICAL SPECIFICATIONS** ( $T_A = 25\text{ }^{\circ}\text{C}$  unless otherwise specified)

| PARAMETER                            | SYMBOL     | TEST CONDITIONS | MIN.     | TYP. | MAX. | UNITS                |
|--------------------------------------|------------|-----------------|----------|------|------|----------------------|
| Thermal resistance, junction-to-case | $R_{thJC}$ |                 | -        | 0.9  | 1.3  | $^{\circ}\text{C/W}$ |
| Marking device                       |            |                 | C20ET07T |      |      |                      |

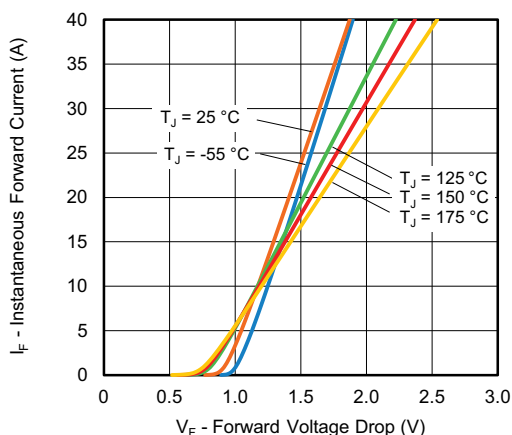


Fig. 1 - Typical Forward Voltage Drop Characteristics

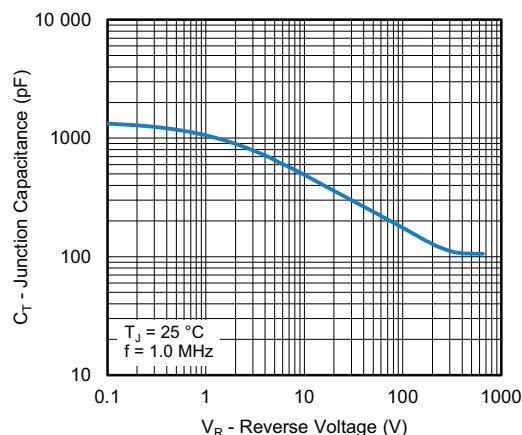


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

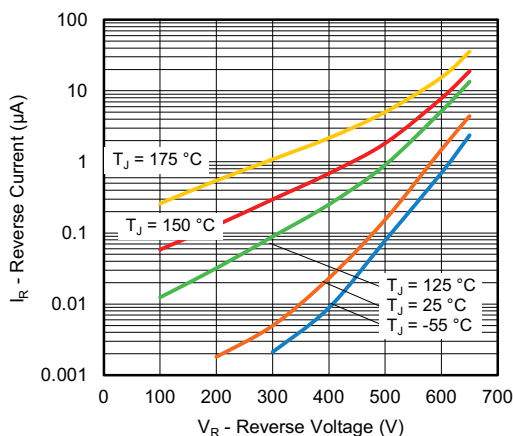


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

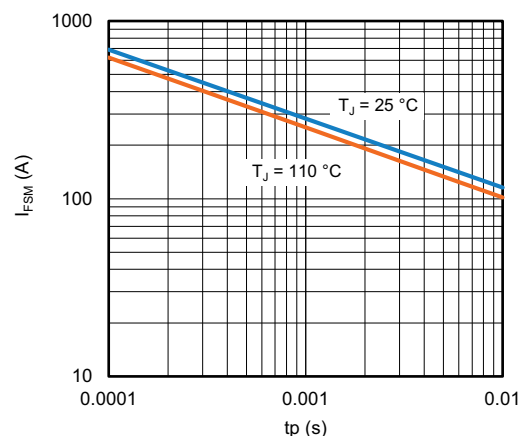


Fig. 4 - Non-Repetitive Peak Forward Surge Current vs. Pulse Duration (Square Wave)

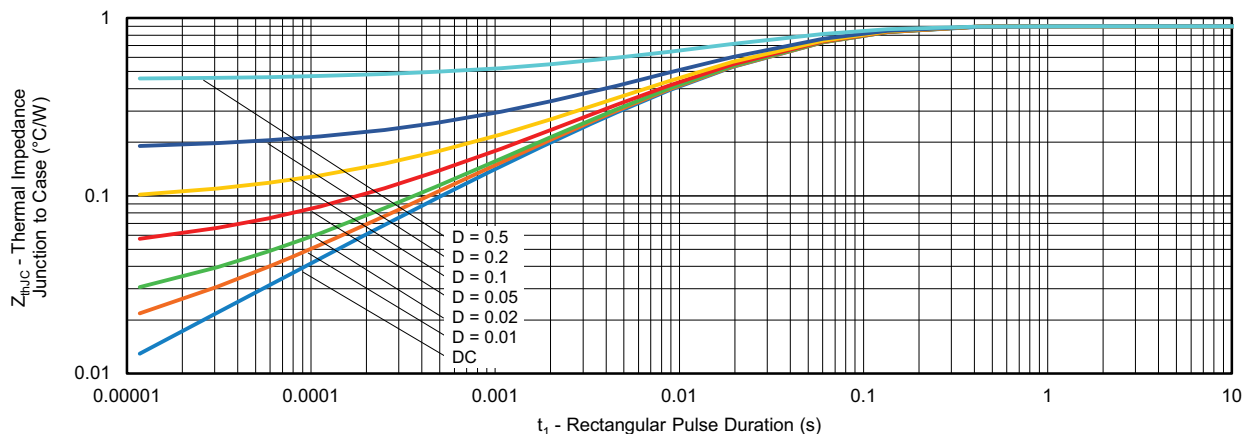
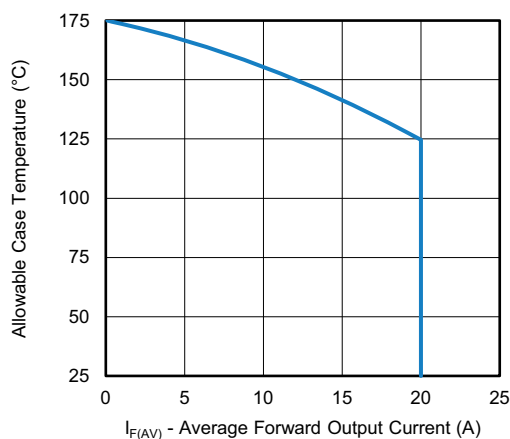

Fig. 5 - Typical Thermal Impedance  $Z_{thJC}$  Characteristics


Fig. 6 - Maximum Allowable Case Temperature vs. Average Forward Current

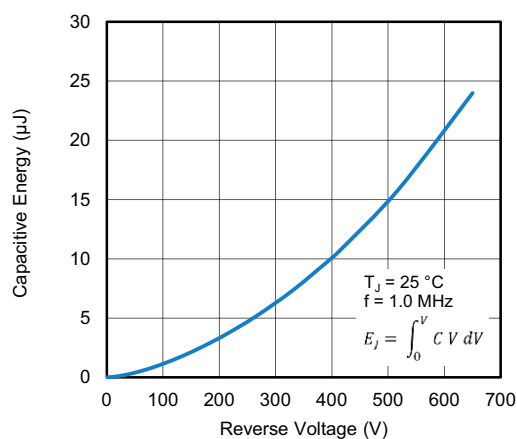


Fig. 8 - Typical Capacitive Energy vs. Reverse Voltage

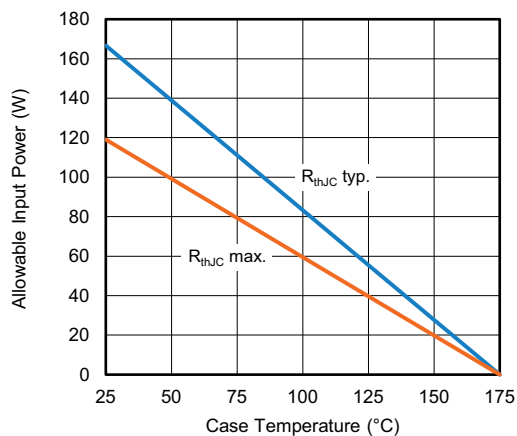


Fig. 7 - Forward Power Loss Characteristics

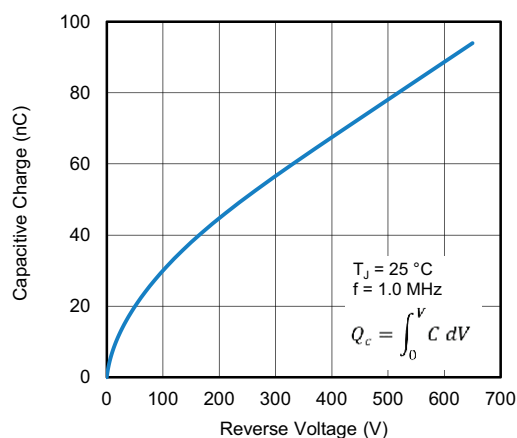


Fig. 9 - Typical Capacitive Charge vs. Reverse Voltage



## ORDERING INFORMATION TABLE

|             |     |   |    |   |   |    |   |     |
|-------------|-----|---|----|---|---|----|---|-----|
| Device code | VS- | C | 20 | E | T | 07 | T | -M3 |
|             | 1   | 2 | 3  | 4 | 5 | 6  | 7 | 8   |

- |   |   |                               |
|---|---|-------------------------------|
| 1 | - | Vishay Semiconductors product |
| 2 | - | C = SiC diode                 |
| 3 | - | Current rating (20 = 20 A)    |
| 4 | - | E = single diode              |
| 5 | - | Package TO-220                |
| 6 | - | Voltage rating: (07 = 650 V)  |
| 7 | - | T = true 2 pin                |
| 8 | - | Environmental digit:          |
- M3 = halogen-free, RoHS-compliant, and termination lead (Pb)-free

## ORDERING INFORMATION

| PREFERRED P/N  | BASE QUANTITY | MINIMUM ORDER QUANTITY | PACKAGING DESCRIPTION    |
|----------------|---------------|------------------------|--------------------------|
| VS-C20ET07T-M3 | 50/tube       | 1000                   | Antistatic plastic tubes |

## LINKS TO RELATED DOCUMENTS

|                          |                                                                        |
|--------------------------|------------------------------------------------------------------------|
| Dimensions               | <a href="http://www.vishay.com/doc?96069">www.vishay.com/doc?96069</a> |
| Part marking information | <a href="http://www.vishay.com/doc?95391">www.vishay.com/doc?95391</a> |
| SPICE model              | <a href="http://www.vishay.com/doc?96834">www.vishay.com/doc?96834</a> |



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